TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

# 2SC4738FT

## Audio Frequency General Purpose Amplifier Applications

Unit: mm

• High Voltage:  $V_{CEO} = 50 \text{ V}$ 

• High Current: IC = 150 mA (max)

• High  $h_{FE}$ :  $h_{FE} = 120 \text{ to } 400$ 

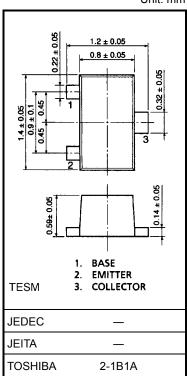
• Excellent hFE Linearity

:  $h_{FE} (I_{C} = 0.1 \text{ mA})/h_{FE} (I_{C} = 2 \text{ mA}) = 0.95 \text{ (typ.)}$ 

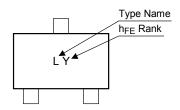
• Complementary to 2SA1832FT

### Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	60	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	Ic	150	mA
Base current	ΙΒ	30	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	-55 to 125	°C



# Marking



# **Electrical Characteristics (Ta = 25°C)**

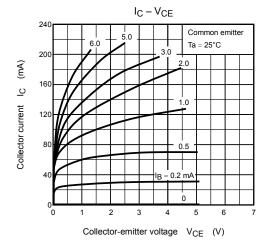
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 60 \text{ V}, I_E = 0$	_	_	0.1	μА
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 5 \text{ V}, I_{C} = 0$			0.1	μΑ
DC current gain	h <sub>FE</sub> (Note)	V <sub>CE</sub> = 6 V, I <sub>C</sub> = 2 mA	120		400	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$	_	0.1	0.25	V
Transition frequency	f <sub>T</sub>	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$	80	_	_	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		2.0	3.5	pF

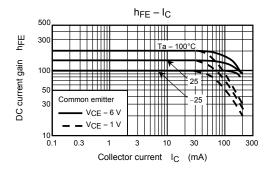
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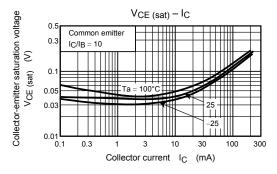
Note: hFE Classification

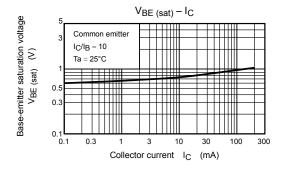
Y (Y): 120 to 240, GR (G): 200 to 400

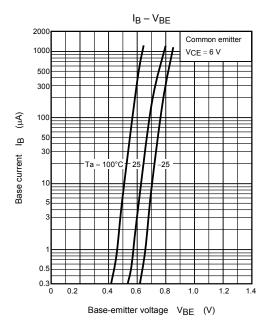
( ) Marking symbol

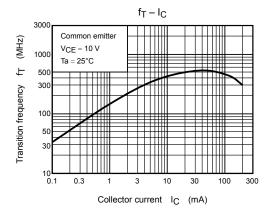


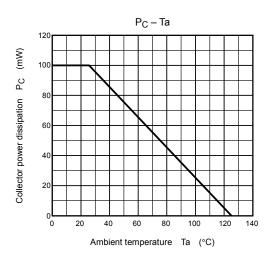












2 2002-01-16

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3 2002-01-16